

Product data sheet

1. General description

Hyperfast power diode in a SOD113 (2-lead TO-220F) plastic package.

2. Features and benefits

- Fast switching
- Isolated plastic package
- Low leakage current
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses in associated MOSFET

3. Applications

- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies

4. Quick reference data

Symbol	Parameter	Conditions	1	Min	Тур	Max	Unit
V _{RRM}	repetitive peak reverse voltage			-	-	600	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _h ≤ 75 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3		-	-	8	A
I _{FRM}	repetitive peak forward current	δ = 0.5 $\ ; t_p$ = 25 $\mu s; T_h \leq$ 75 °C; square-wave pulse		-	-	16	A
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4		-	-	91	A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4		-	-	100	A
Static char	acteristics	· · · · ·				1	
V _F	forward voltage	I _F = 8 A; T _j = 25 °C; <u>Fig. 6</u>		-	-	3.4	V
		I _F = 8 A; T _j = 125 °C; <u>Fig. 6</u>		-	1.5	1.9	V
		I _F = 8 A; T _j = 150 °C		-	1.4	-	V





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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Dynamic characteristics							
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	12	18	ns
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; \text{ d}_F/\text{d}t = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$		-	19	-	ns

5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode	mb	K-HA-A
2	А	anode		001aaa020
mb	n.c.	mounting base; isolated	TO-220F (SOD113)	

6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
BYC8X-600P	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack"	SOD113				

7. Marking

Table 4. Marking codes	
Type number	Marking code
BYC8X-600P	BYC8X-600P

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V _{RRM}	repetitive peak reverse voltage		-	600	V
V _{RWM}	crest working reverse voltage		-	600	V
V _R	reverse voltage	DC	-	600	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _h ≤ 75 °C; square-wave pulse; <u>Fig. 1; Fig. 2</u> ; <u>Fig. 3</u>	-	8	A
I _{FRM}	repetitive peak forward current	δ = 0.5 $\ ; t_p$ = 25 $\mu s; \ T_h \leq$ 75 °C; square-wave pulse	-	16	A
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	91	A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	100	A
T _{stg}	storage temperature		-65	175	°C
Tj	junction temperature		-	175	°C

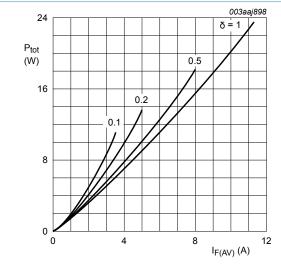


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$ $V_{O} = 1.581 \text{ V}; \text{ } \text{R}_{\text{S}} = 0.043 \text{ } \Omega$

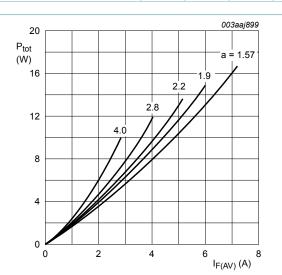


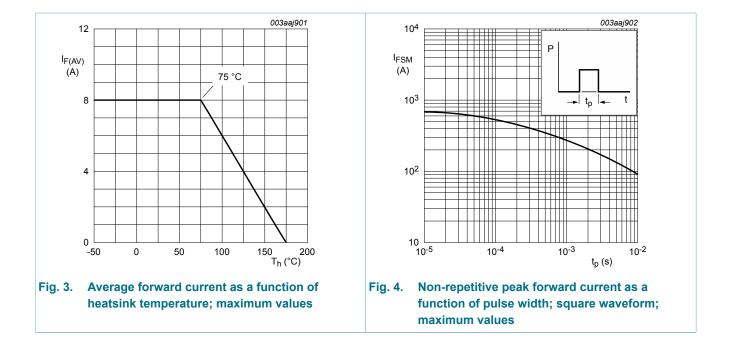
Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

$$\begin{split} \mathbf{a} &= \mathbf{form} \; \mathbf{factor} = I_{F(RMS)} / I_{F(AV)} \\ \mathbf{V}_{\mathrm{O}} &= \mathbf{1.581} \; \mathrm{V}; \; \mathbf{R}_{\mathrm{S}} = \mathbf{0.043} \; \Omega \end{split}$$

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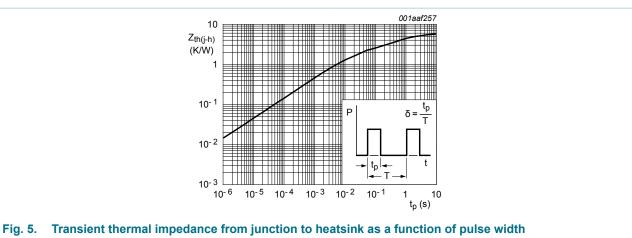
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9. Thermal characteristics

Table 6. T	hermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-h)}	thermal resistance	without heatsink compound	-	-	7.2	K/W
	from junction to heatsink	with heatsink compound; Fig. 5	-	-	5.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air		-	60	-	K/W



10. Isolation characteristics

Table 7. Isolation characteristics							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	50 Hz \leq f \leq 60 Hz; RH \leq 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free		-	-	2500	V
C _{isol}	isolation capacitance	from cathode to external heatsink		-	10	-	pF

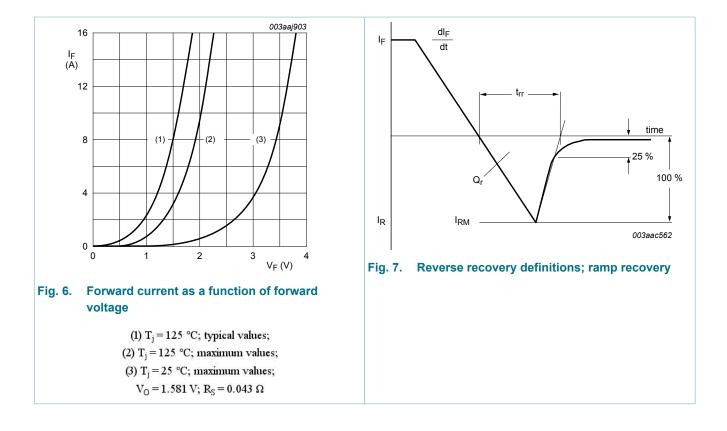
11. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static char	acteristics					
V _F	forward voltage	I _F = 8 A; T _j = 25 °C; <u>Fig. 6</u>	-	-	3.4	V
		I _F = 8 A; T _j = 125 °C; <u>Fig. 6</u>	-	1.5	1.9	V
		I _F = 8 A; T _j = 150 °C	-	1.4	-	V
I _R reve	reverse current	V _R = 600 V; T _j = 25 °C	-	-	20	μA
		V _R = 600 V; T _j = 125 °C	-	-	200	μA
Dynamic c	haracteristics	I	I			
Q _r	recovered charge	$I_{F} = 8 \text{ A}; V_{R} = 200 \text{ V}; dI_{F}/dt = 200 \text{ A}/\mu\text{s};$ $T_{j} = 25 \text{ °C}; \underline{\text{Fig. 7}}$	-	17	-	nC
		$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	90	-	nC
t _{rr}	reverse recovery time	I _F = 1 A; V _R = 30 V; dI _F /dt = 200 A/μs; T _j = 25 °C; <u>Fig. 7</u>	-	12	18	ns
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	19	-	ns
I _{RM}	peak reverse recovery current	$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	2.2	A
		I _F = 8 A; V _R = 200 V; dI _F /dt = 200 A/μs; T _i = 125 °C; <u>Fig. 7</u>	-	-	6	A

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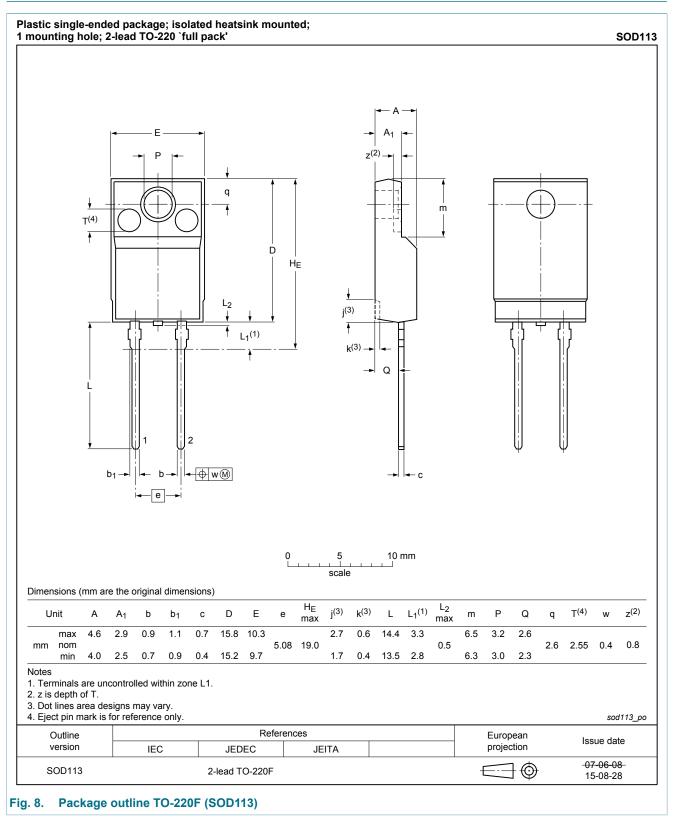
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12. Package outline



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Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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